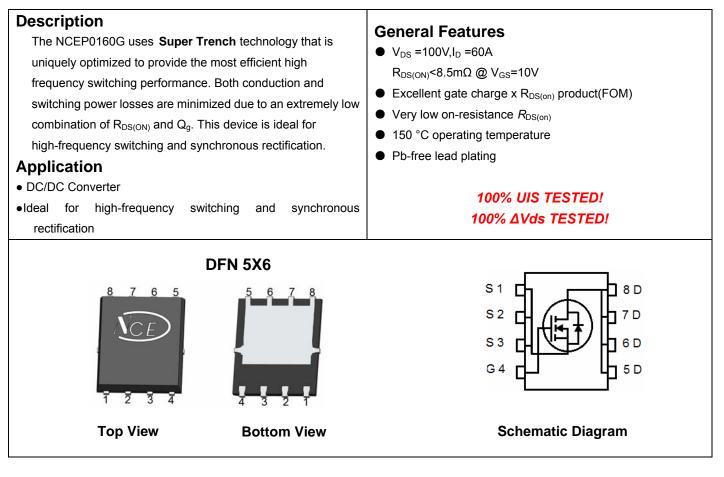


# NCE N-Channel Super Trench Power MOSFET



### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P0160G	NCEP0160G	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings (T<sub>c</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous <sup>(Note 1)</sup> (Package Limited)	Ι <sub>D</sub>	60	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	l <sub>D</sub> (100℃)	42.5	A
Pulsed Drain Current	I <sub>DM</sub>	240	A
Maximum Power Dissipation	P <sub>D</sub>	105	W
Derating factor		0.84	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	250	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	°C

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	1.2	°C/W
Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	50	°C/W



### Electrical Characteristics (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)	<b>I</b>		•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_D=250\mu A$	2.5	-	4.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =10V, I <sub>D</sub> =30A	-	-	8.5	mΩ
Gate resistance	R <sub>G</sub>		-	8	-	Ω
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =30A	40	-	-	S
Dynamic Characteristics (Note4)			-			
Input Capacitance	C <sub>lss</sub>		-	3500	-	PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =0V, F=1.0MHz	-	600	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	29	-	PF
Switching Characteristics (Note 4)	····					
Turn-on Delay Time	t <sub>d(on)</sub>		-	12	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =50V,I <sub>D</sub> =30A	-	45	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$	-	31	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg	)/ _===0)/   _===0.0	-	48		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =50V,I <sub>D</sub> =30A,	-	15		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	8		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =60A	-		1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	60	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J$ = 25°C, $I_F$ = $I_S$	-	55		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	93		nC

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm2 (one layer, 70  $\mu m$  thick) copper area for drain

connection. PCB is vertical in still air.

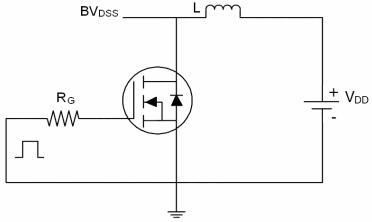
3. Pulse Test: Pulse Width ≤ 300 $\mu$ s, Duty Cycle ≤ 2%.

4. Guaranteed by design, not subject to production

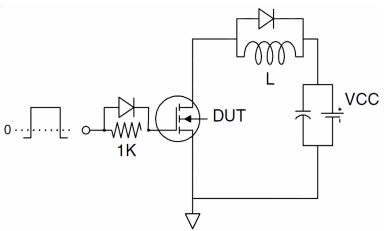
5. EAS condition : Tj=25  $^\circ \!\! \mathrm{C}$  ,V\_DD=50V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$ 



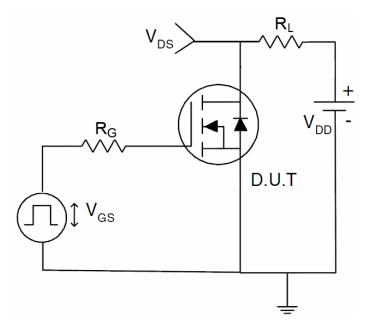
### Test Circuit 1) E<sub>AS</sub> test Circuit



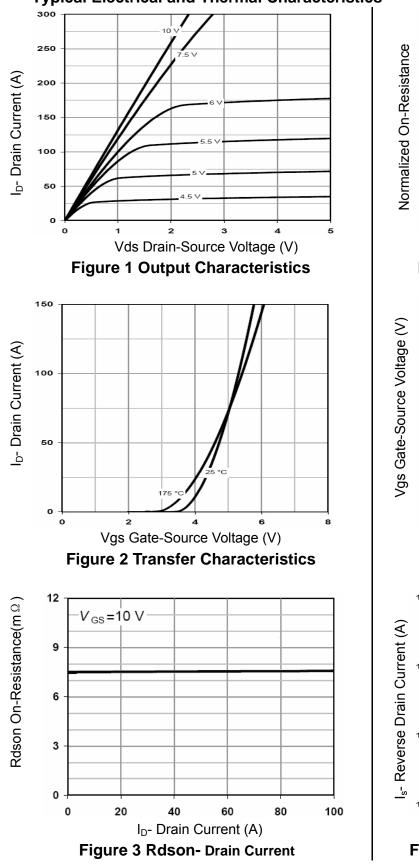
### 2) Gate charge test Circuit



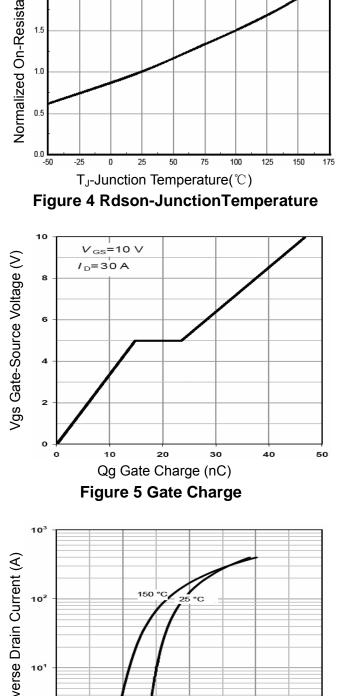
3) Switch Time Test Circuit





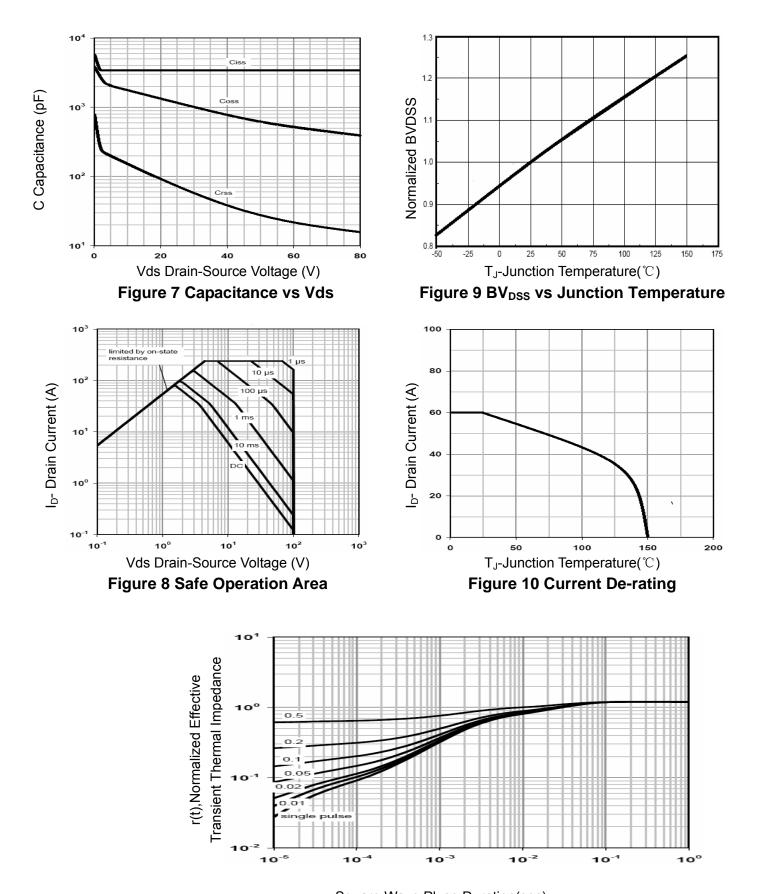


**Typical Electrical and Thermal Characteristics** 2.5 V<sub>GS</sub>=10 V I<sub>D</sub>=30 A 2.0





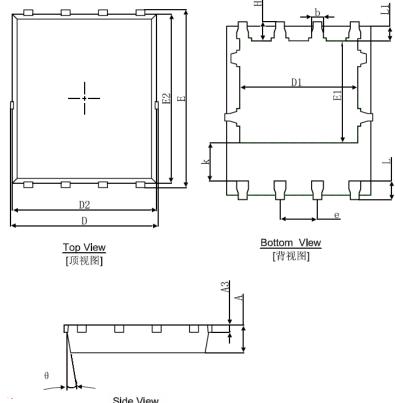
#### http://www.ncepower.com



Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



## DFN5X6-8L Package Information



<u>Side View</u> [侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	0.900	1.000	0.035	0.039	
A3	0.254	REF.	0.010REF.		
D	4.944	5.096	0.195	0.201	
E	5.974	6.126	0.235	0.241	
D1	3.910	4.110	0.154	0.162	
E1	3.375	3.575	0.133	0.141	
D2	4.824	4.976	0.190	0.196	
E2	5.674	5.826	0.223	0.229	
k	1.190	1.390	0.047	0.055	
b	0.350	0.450	0.014	0.018	
е	1.270TYP.		0.050TYP.		
L	0.559	0.711	0.022	0.028	
L1	0.424	0.576	0.017	0.023	
Н	0.574	0.726	0.023	0.029	
θ	8°	12°	8°	12°	



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